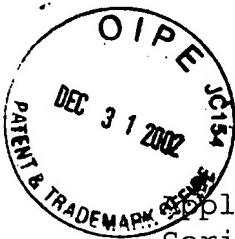


2814



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Kusumoto, et al. Art Unit : 2814
 Serial No.: 09/941,367 Examiner : Theresa T. Doan
 Filed : August 28, 2001
 Title : METHOD FOR PRODUCING INSULATED GATE THIN FILM
 SEMICONDUCTOR DEVICE

#100 Audit
 M. Brunson
 1/9/03

Commissioner for Patents
 Washington, D.C. 20231

RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Responsive to the action mailed November 26, 2002,
 applicants elect the invention of Group I drawn to the
 embodiment of claims 1, 2, 9-10 and 17-20. The election is made
without traverse.

Further, applicants wish to amend the application as
 follows:

In the claims:Please amend claims 17-20 as follows:

-- 17. A method according to any one of claims 1, 2, 9 and
 10, wherein said semiconductor layer comprises amorphous
 silicon.

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